

## Silicon Standard Recovery Diode

$V_{RRM} = 50\text{ V} - 600\text{ V}$   
 $I_F = 15\text{ A}$

### Features

- High Surge Capability
- Types up to 600 V  $V_{RRM}$

DO-5 Package



### Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	1N3208 (R)	1N3209 (R)	1N3210 (R)	1N3211 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		50	100	200	300	V
RMS reverse voltage	$V_{RMS}$		35	70	140	210	V
DC blocking voltage	$V_{DC}$		50	100	200	300	V
Continuous forward current	$I_F$	$T_C \leq 150\text{ °C}$	15	15	15	15	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	297	297	297	297	A
Operating temperature	$T_j$		-65 to 175	-65 to 175	-65 to 175	-65 to 175	°C
Storage temperature	$T_{stg}$		-65 to 175	-65 to 175	-65 to 175	-65 to 175	°C

### Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	1N3208 (R)	1N3209 (R)	1N3210 (R)	1N3211 (R)	Unit
Diode forward voltage	$V_F$	$I_F = 15\text{ A}$ , $T_j = 25\text{ °C}$	1.5	1.5	1.5	1.5	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ °C}$	10	10	10	10	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 150\text{ °C}$	10	10	10	10	mA

### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		0.65	0.65	0.65	0.65	°C/W
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